



NO CONTENT ON THE ATTACHED DOCUMENT HAS CHANGED



THIS PAGE INTENTIONALLY LEFT BLANK



MICROWAVE CORPORATION v04.0412



HMC-AUH320

GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 71 - 86 GHz

Typical Applications

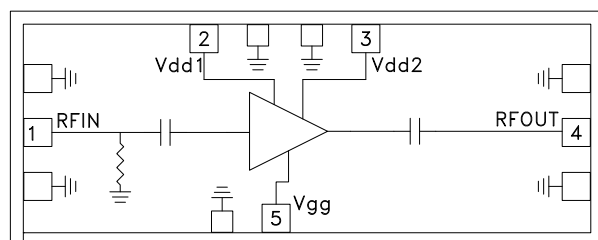
This HMC-AUH320 is ideal for:

- Short Haul / High Capacity Links
- Wireless LAN Bridges
- Automotive Radar
- Military & Space
- E-Band Communication Systems

Features

Gain: 16 dB @ 74 GHz
P1dB: +15 dBm
Supply Voltage: +4V
50 Ohm Matched Input/Output
Die Size: 2.20 x 0.87 x 0.1 mm

Functional Diagram



General Description

The HMC-AUH320 is a high dynamic range, four stage GaAs HEMT MMIC Medium Power Amplifier which operates between 71 and 86 GHz. The HMC-AUH320 provides 16 dB of gain at 74 GHz, and an output power of +15 dBm at 1 dB compression from a +4V supply voltage. All bond pads and the die backside are Ti/Au metallized and the amplifier device is fully passivated for reliable operation. The HMC-AUH320 GaAs HEMT MMIC Medium Power Amplifier is compatible with conventional die attach methods, as well as thermocompression and thermosonic wire bonding, making it ideal for MCM and hybrid microcircuit applications. All data shown herein is measured with the chip in a 50 Ohm environment and RF probes contacting the die pads.

Electrical Specifications, $T_A = +25^\circ \text{C}$, $V_{dd1}=V_{dd2} = 4\text{V}$, $I_{dd1}+I_{dd2} = 130\text{mA}$ [2]

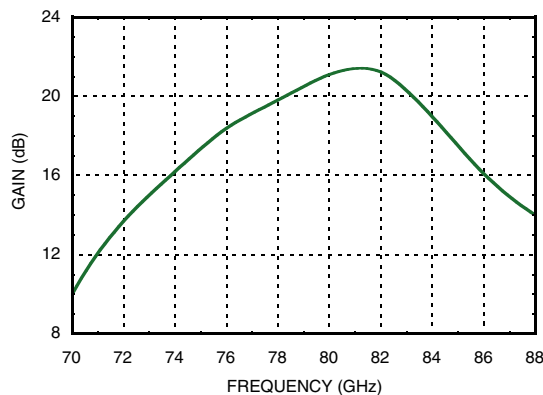
Parameter	Min.	Typ.	Max.	Units
Frequency Range	71 - 86			GHz
Gain	10	16		dB
Input Return Loss		4		dB
Output Return Loss		6		dB
Output power for 1dB Compression (P1dB)		15		dBm
Saturated Output Power (Psat)		16		dBm
Supply Current (Idd1+Idd2)		130		mA

[1] Unless otherwise indicated, all measurements are from probed die

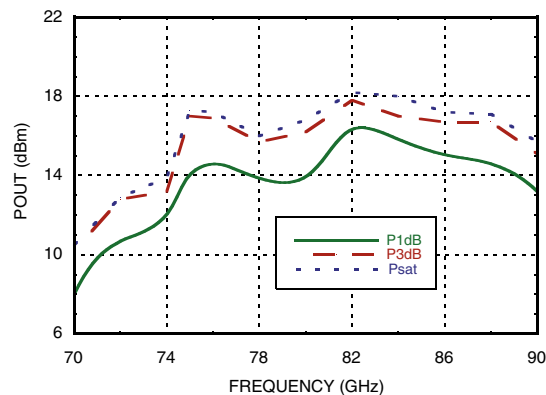
[2] Adjust Vgg between -0.8V to +0.3V (typ -0.1V) to achieve Idd₁ = 40mA, Idd₂ = 90mA or Idd_{total} = 130 mA.

GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 71 - 86 GHz

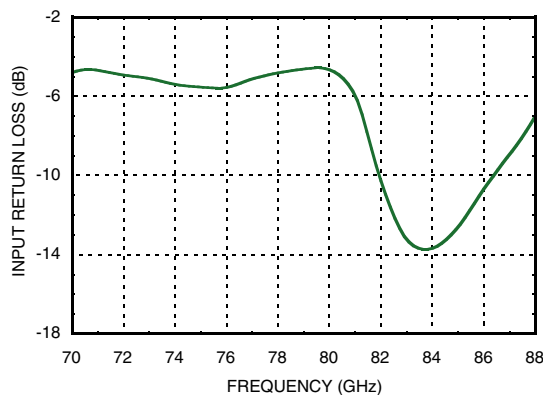
Linear Gain vs. Frequency



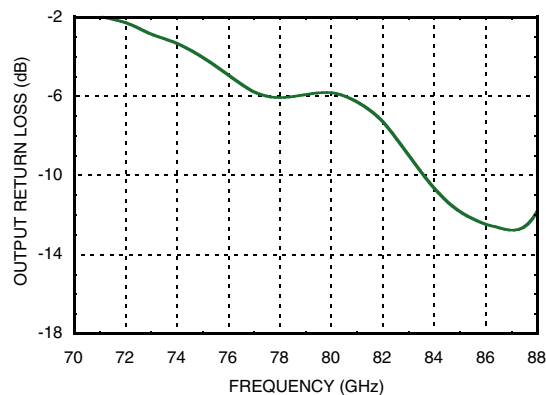
Fixtured Output Power vs. Frequency



Input Return Loss vs. Frequency



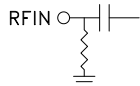
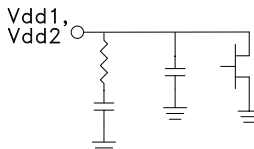
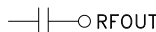
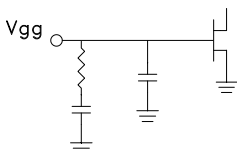
Output Return Loss vs. Frequency



Note: Measured Performance Characteristics (Typical Performance at 25°C) Vdd1 = Vdd2 = 4V and Idd1 = 40mA, Idd2 = 90mA

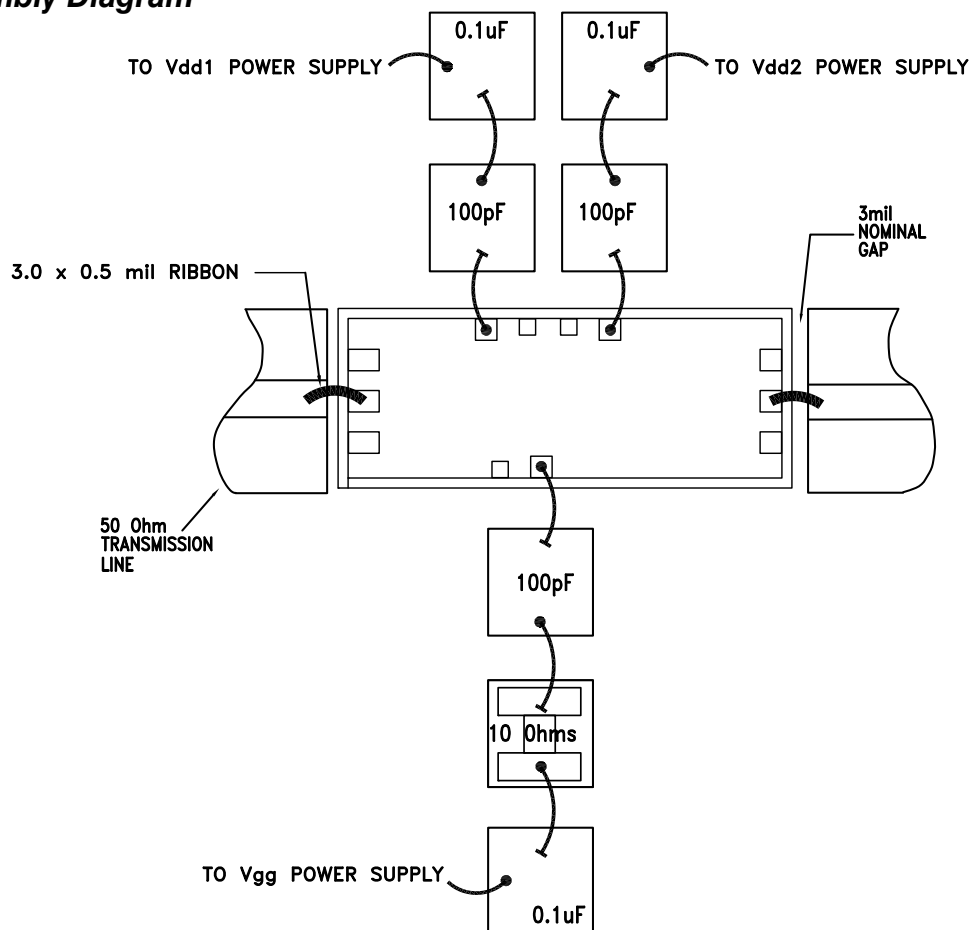
GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 71 - 86 GHz

Pad Descriptions

Pad Number	Function	Description	Interface Schematic
1	RFIN	This pad is DC coupled (for ESD) and matched to 50 Ohms.	
2, 3	Vdd1, Vdd2	Power Supply Voltage for the amplifier. See assembly for required external components.	
4	RFOUT	This pad is AC coupled and matched to 50 Ohms.	
5	Vgg	Gate control for amplifier. See Assembly Drawing for required external components. Please follow "MMIC Amplifier Biasing Procedure" application note.	
Die Bottom	GND	Die bottom must be connected to RF/DC ground.	

GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 71 - 86 GHz

Assembly Diagram



Note 1: Bypass caps should be 100 pF (approximately) ceramic (single-layer) placed no farther than 30 mils from the amplifier

Note 2: Best performance obtained from use of <10 mil (long) by 3 by 0.5mil ribbons on input and output.

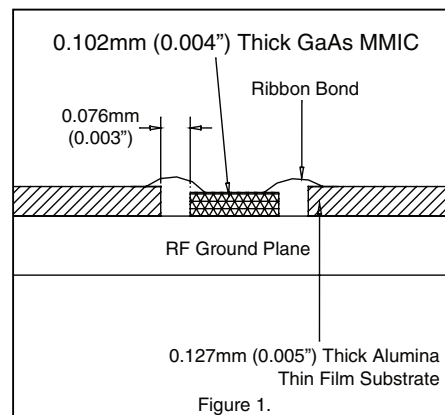
GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 71 - 86 GHz

Mounting & Bonding Techniques for Millimeterwave GaAs MMICs

The die should be attached directly to the ground plane eutectically or with conductive epoxy (see HMC general Handling, Mounting, Bonding Note).

50 Ohm Microstrip transmission lines on 0.127mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 1). If 0.254mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.150mm (6 mils) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102mm (4 mil) thick die to a 0.150mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 2).

Microstrip substrates should be placed as close to the die as possible in order to minimize bond wire length. Typical die-to-substrate spacing is 0.076mm to 0.152 mm (3 to 6 mils).



Handling Precautions

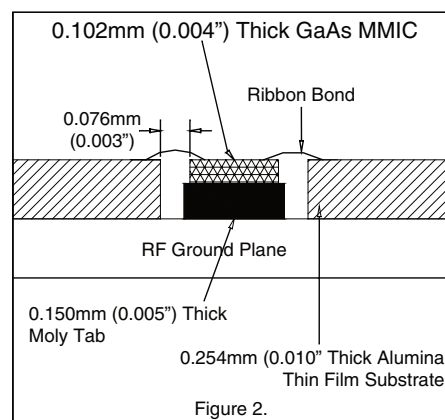
Follow these precautions to avoid permanent damage.

Storage: All bare die are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

Cleanliness: Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

Static Sensitivity: Follow ESD precautions to protect against ESD strikes.

Transients: Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.



General Handling: Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip may have fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

Mounting

The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

Eutectic Die Attach: A 80/20 gold tin preform is recommended with a work surface temperature of 255 °C and a tool temperature of 265 °C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 °C. DO NOT expose the chip to a temperature greater than 320 °C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

Epoxy Die Attach: Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule.

Wire Bonding

RF bonds made with 0.003" x 0.0005" ribbon are recommended. These bonds should be thermosonically bonded with a force of 40-60 grams. DC bonds of 0.001" (0.025 mm) diameter, thermosonically bonded, are recommended. Ball bonds should be made with a force of 40-50 grams and wedge bonds at 18-22 grams. All bonds should be made with a nominal stage temperature of 150 °C. A minimum amount of ultrasonic energy should be applied to achieve reliable bonds. All bonds should be as short as possible, less than 12 mils (0.31 mm).

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru